

Si Photo Diode Chip--ORT-2151PD

1. Scope:

- The specification applies to NIP silicon photo-diode chips.
- Type: ORT-2151PD

2. Structure:

- NIP planar type.
- Top (Cathode) Side: aluminum(Al) alloy.
- Back (Anode) Side: silver(Ag) alloy.

3. Size: (51mil×51mil)

- Chip size : $(1270\mu\text{m} \times 1270\mu\text{m}) \pm 40\mu\text{m}$ (include scribe line)
- Chip thickness : $280\mu\text{m} \pm 20\mu\text{m}$
- Active area : $(1110\mu\text{m} \times 1110\mu\text{m}) \pm 20\mu\text{m}$
- Pad size : $(254\mu\text{m} \times 200\mu\text{m}) \pm 10\mu\text{m}$
- Pattern drawing: per fig. 1

4. Electro-Optical Characteristics:

(Ta=+25℃)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F=10\text{mA}$, $H=0$	0.5		1.3	V
Reverse Breakdown voltage	V_{BR}	$I_R=100\mu\text{A}$, $H=0$	35			V
Reverse Dark Current	I_D	$V_R=10\text{V}$, $H=0$			10	nA
Light Current	I_L	$V_R=5\text{V}$, Has $1\text{mw}/\text{cm}^2$, @ 940nm		47		μA
Peak Sensing wavelength	λ_p			940		nm

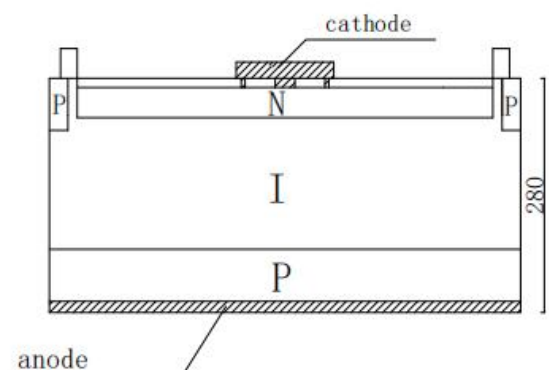
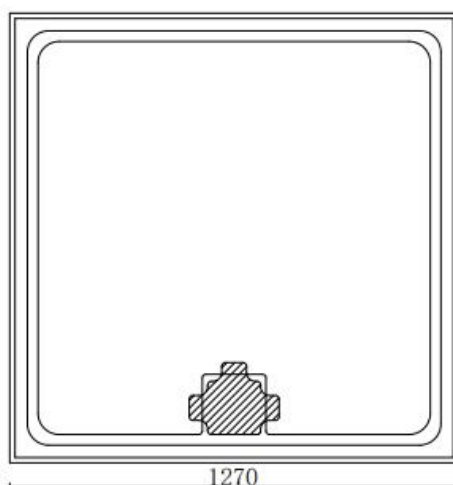


fig.1

5. Spectral Response

